



# ECH8310

## P-Channel Power MOSFET -30V, -9A, 17mΩ, Single ECH8

ON Semiconductor®

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### Features

- 4V drive
- Halogen free compliance
- Protection diode in

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

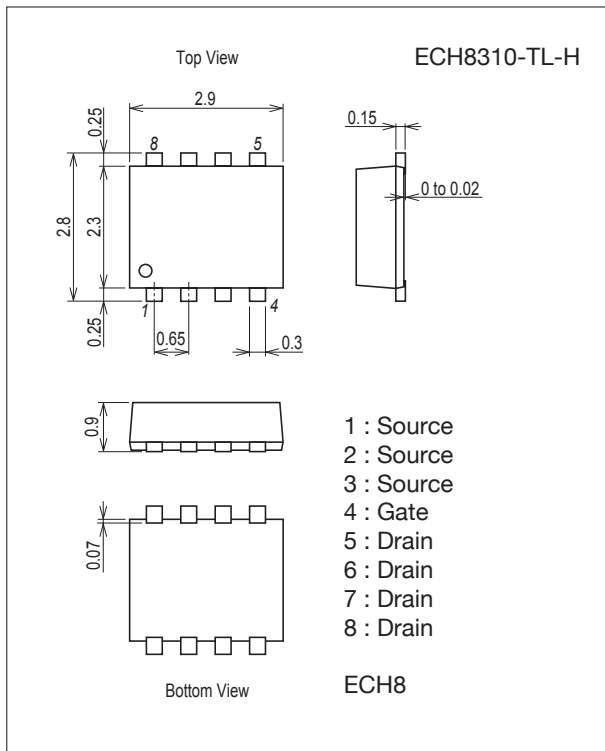
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-9	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-60	A
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### Package Dimensions

unit : mm (typ)

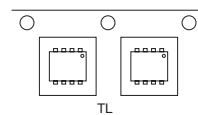
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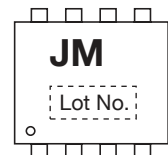
### Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

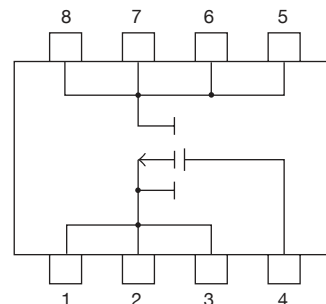
### Packing Type : TL



### Marking



### Electrical Connection



### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

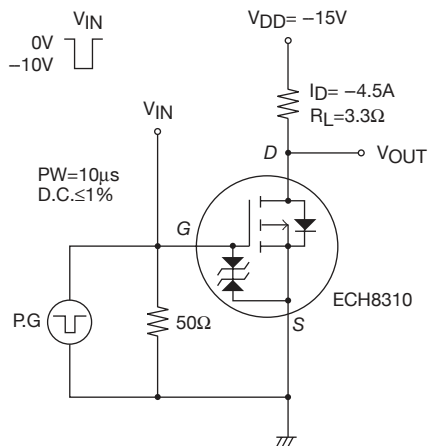
# ECH8310

## Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4.5A		12		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-4.5A, V <sub>GS</sub> =-10V	9	13	17	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-2A, V <sub>GS</sub> =-4.5V	12	20	28	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-2A, V <sub>GS</sub> =-4.0V	13.5	23	32.5	mΩ
Input Capacitance	C <sub>iss</sub>			1400		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-10V, f=1MHz		350		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			250		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		10		ns
Rise Time	t <sub>r</sub>			45		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>			134		ns
Fall Time	t <sub>f</sub>			87		ns
Total Gate Charge	Q <sub>g</sub>				28	
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-9A		4		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>			6		nC
Diode Forward Voltage	V <sub>SD</sub>		I <sub>S</sub> =-9A, V <sub>GS</sub> =0V		-0.8	-1.2

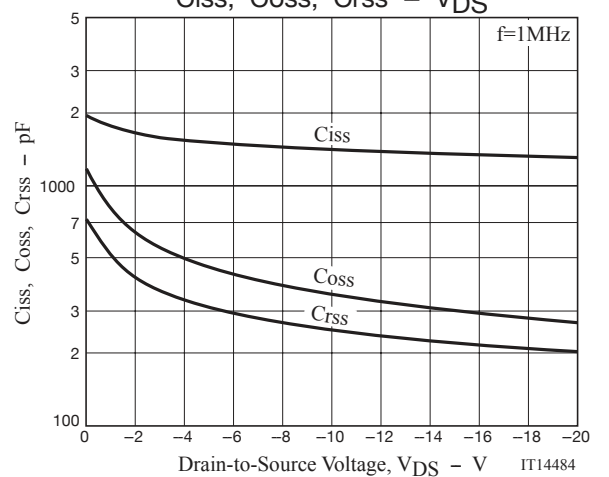
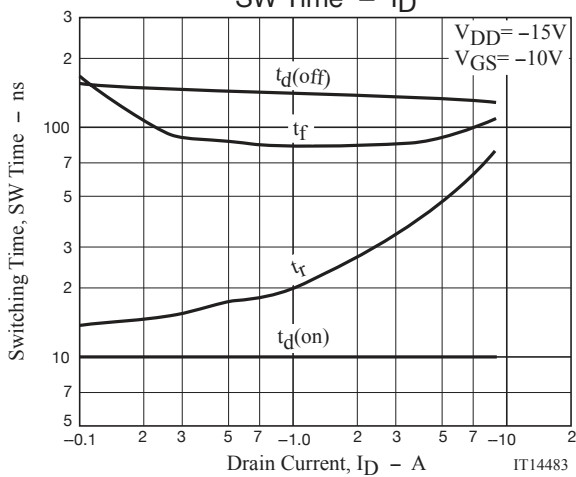
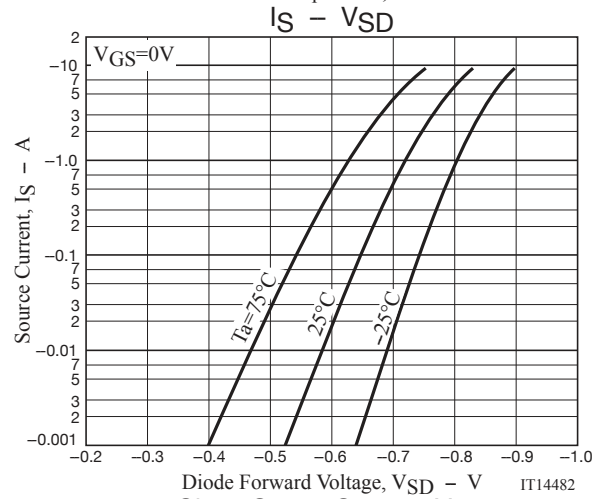
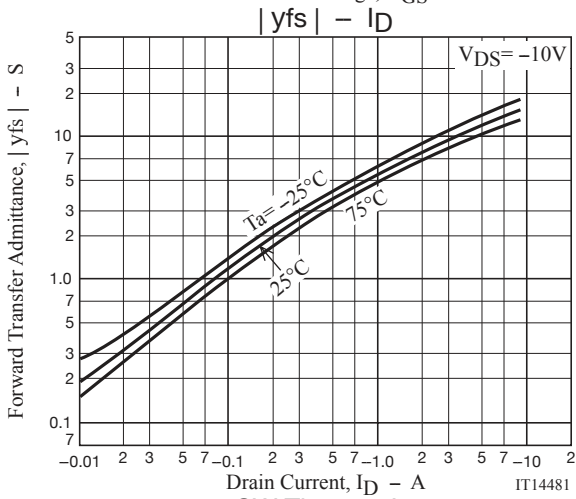
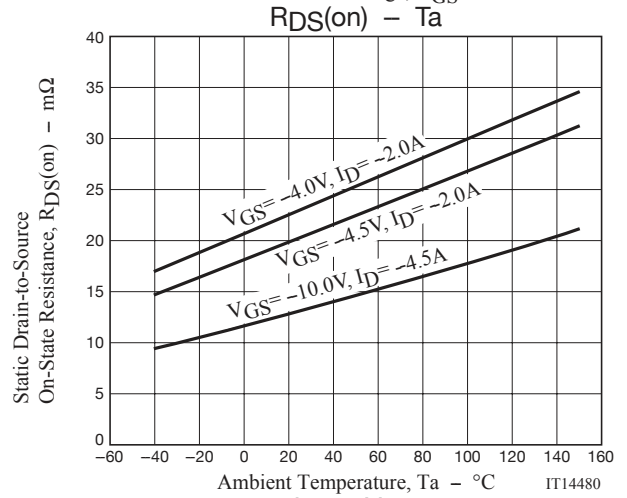
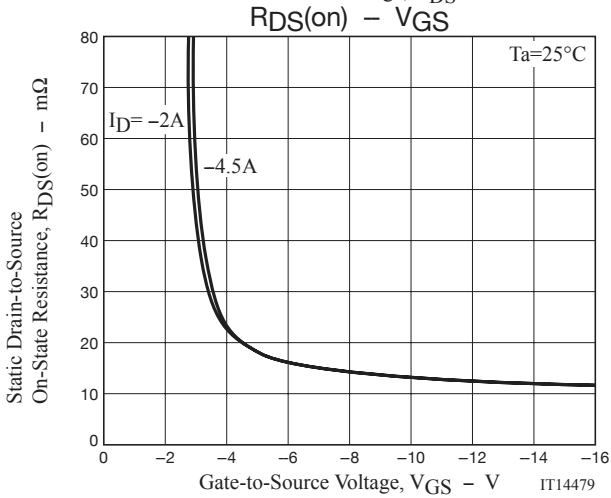
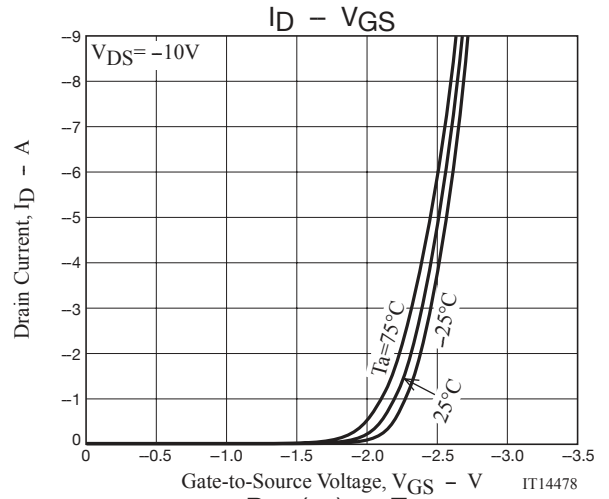
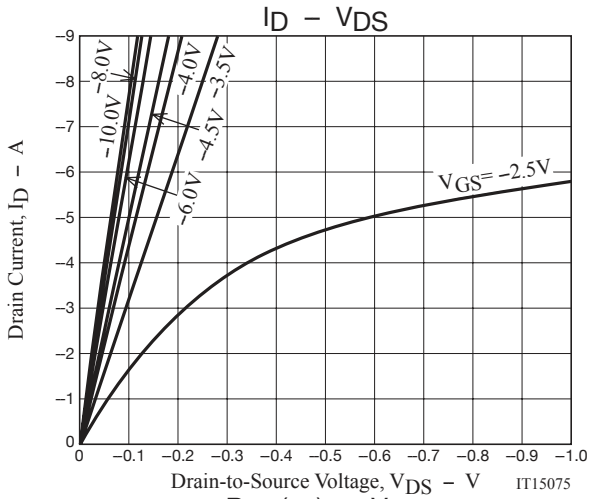
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

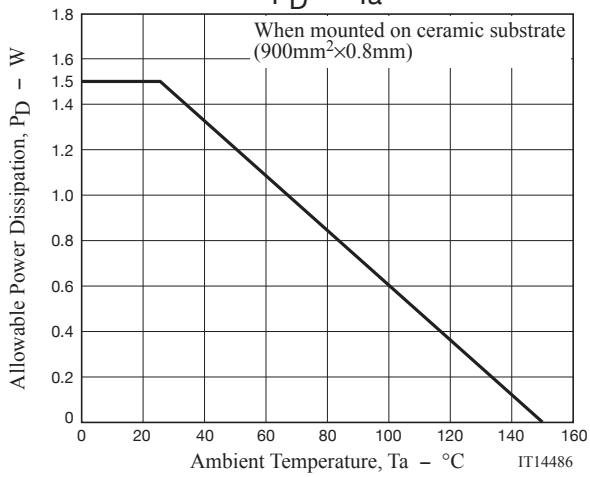
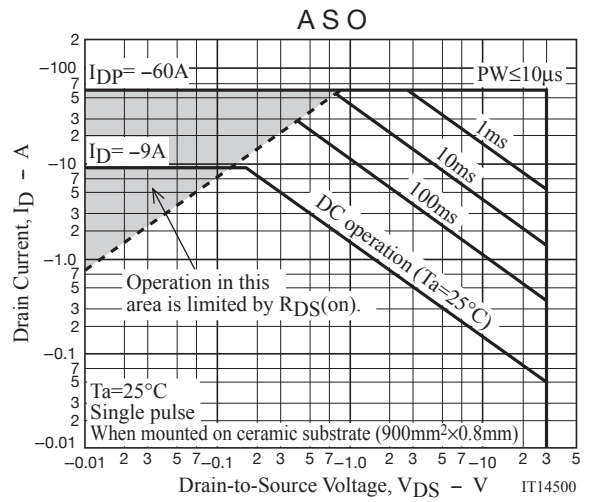
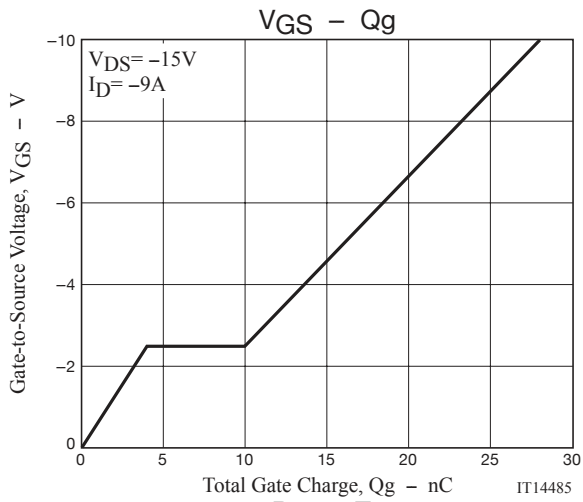
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
ECH8310-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free

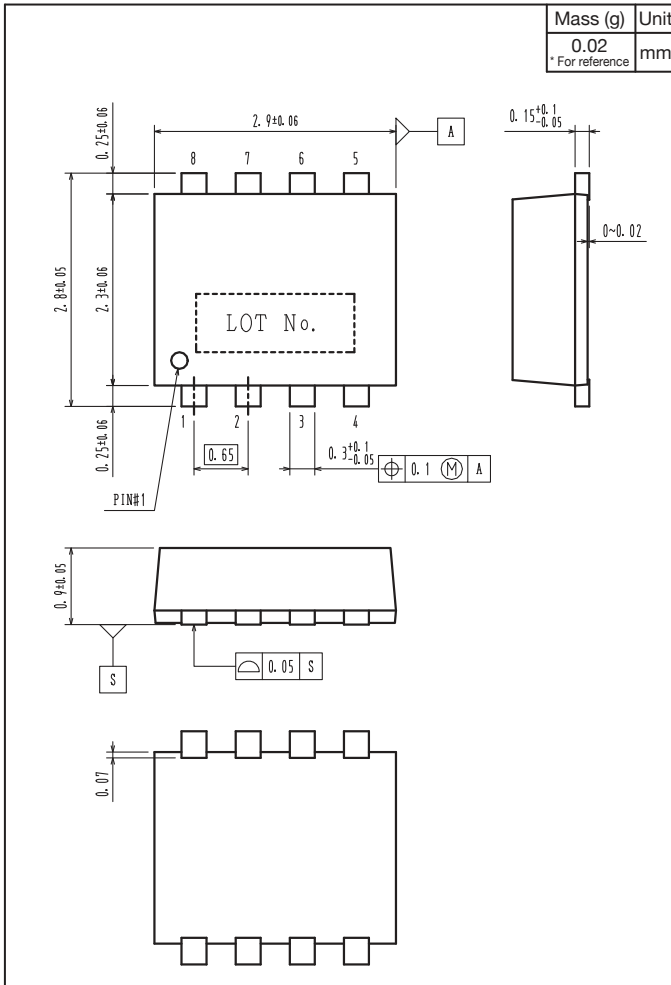




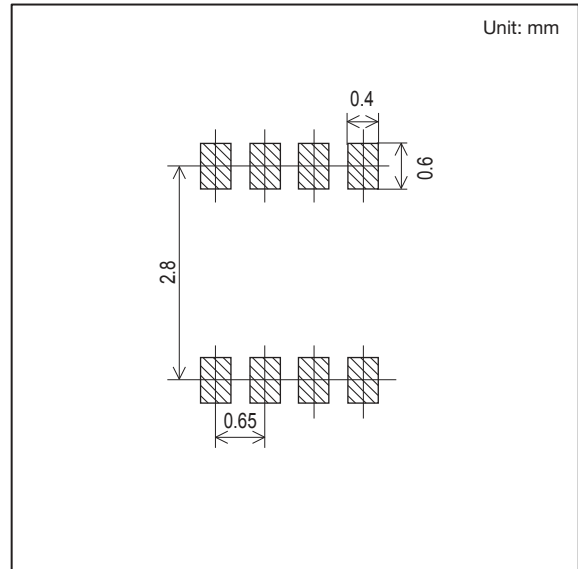
# ECH8310

## Outline Drawing

ECH8310-TL-H



## Land Pattern Example



Note on usage : Since the ECH8310 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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